

Quad SPST CMOS Analog Switches

DESCRIPTION

The DG441, DG442 monolithic quad analog switches are designed to provide high speed, low error switching of analog and audio signals. The DG441 has a normally closed function. The DG442 has a normally open function. Combining low on-resistance (50 Ω , typ.) with high speed (t_{ON} 150 ns, typ.), the DG441, DG442 are ideally suited for upgrading DG201A/202 sockets. Charge injection has been minimized on the drain for use in sample-and-hold circuits.

To achieve high voltage ratings and superior switching performance, the DG441, DG442 are built on Vishay Siliconix's high-voltage silicon-gate process. An epitaxial layer prevents latchup.

Each switch conducts equally well in both directions when on, and blocks input voltages to the supply levels when off.

FEATURES

- **Halogen-free according to IEC 61249-2-21 Definition**
- Low on-resistance: 50 Ω
- Low leakage: 80 pA
- Low power consumption: 0.2 mW
- Fast switching action - t_{ON} : 150 ns
- Low charge injection - Q: - 1 pC
- DG201A/DG202 upgrades
- TTL/CMOS-compatible logic
- Single supply capability
- **Compliant to RoHS Directive 2002/95/EC**



RoHS
COMPLIANT
HALOGEN
FREE

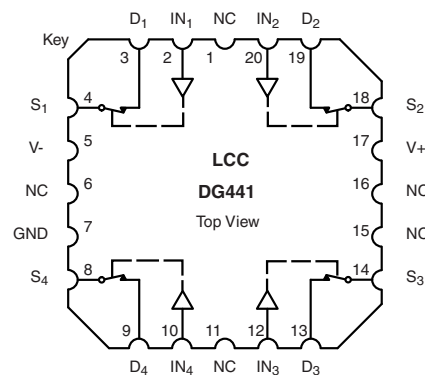
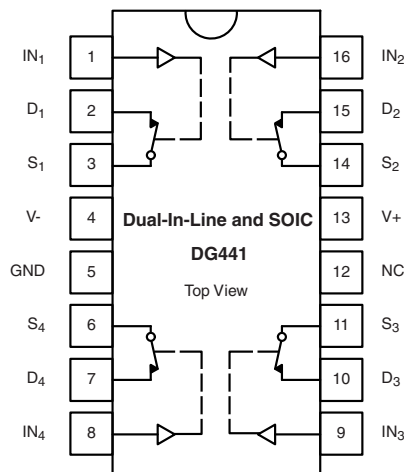
BENEFITS

- Less signal errors and distortion
- Reduced power supply requirements
- Faster throughput
- Improved reliability
- Reduced pedestal errors
- Simplifies retrofit
- Simple interfacing

APPLICATIONS

- Audio switching
- Battery powered systems
- Data acquisition
- Hi-Rel systems
- Sample-and-hold circuits
- Communication systems
- Automatic test equipment
- Medical instruments

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE

Logic	DG441	DG442
0	On	Off
1	Off	On

Logic "0" $\leq$ 0.8 V

Logic "1" $\geq$ 2.4 V

ORDERING INFORMATION

Temp. Range	Package	Part Number
- 40 °C to 85 °C	16-pin plastic DIP	DG441DJ
		DG441DJ-E3
	16-pin narrow SOIC	DG442DJ
		DG442DJ-E3
		DG441DY
		DG441DY-E3
		DG441DY-T1
		DG441DY-T1-E3
		DG442DY
		DG442DY-E3
		DG442DY-T1
		DG442DY-T1-E3

ABSOLUTE MAXIMUM RATINGS

Parameter		Limit	Unit
V+ to V-		44	V
GND to V-		25	
Digital Inputs ^a , V _S , V _D		(V-) - 2 to (V+) + 2 or 30 mA, whichever occurs first	
Continuous Current (any terminal)		30	mA
Current, S or D (pulsed at 1 ms, 10 % duty cycle)		100	
Storage Temperature	(AK suffix)	- 65 to 150	°C
	(DJ, DY suffix)	- 65 to 125	
Power Dissipation (Package) ^b	16-pin plastic DIP ^c	450	mW
	16-pin CerDIP ^d	900	
	16-pin narrow SOIC ^d	900	
	LCC-20 ^d	1200	

Notes:

a. Signals on S_X, D_X, or IN_X exceeding V₊ or V₋ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. All leads welded or soldered to PC board.

c. Derate 6 mW/°C above 75 °C.

d. Derate 12 mW/°C above 75 °C.

SCHEMATIC DIAGRAM Typical Channel

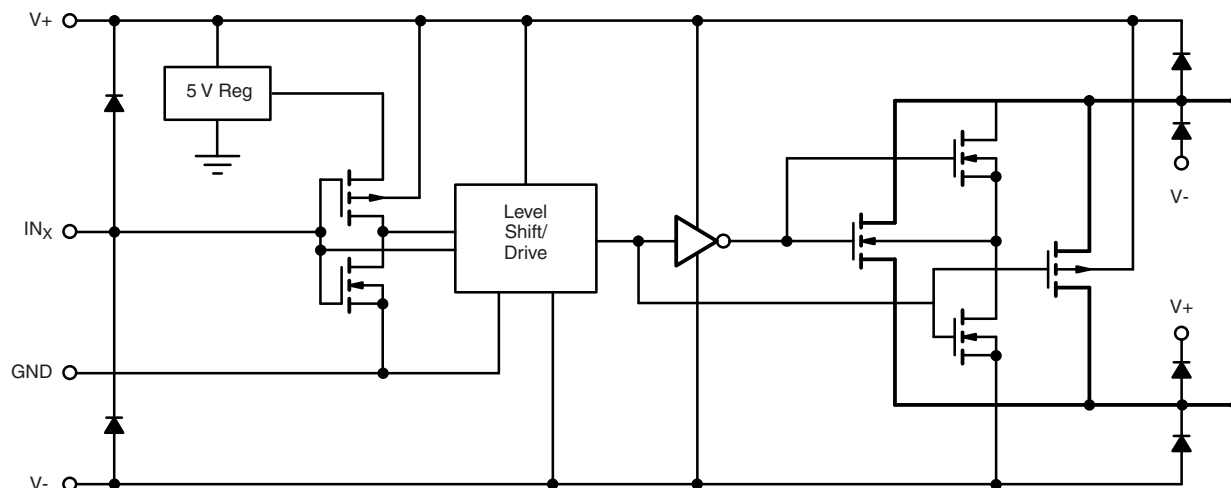


Figure 1.

**SPECIFICATIONS^a** (Dual Supplies)

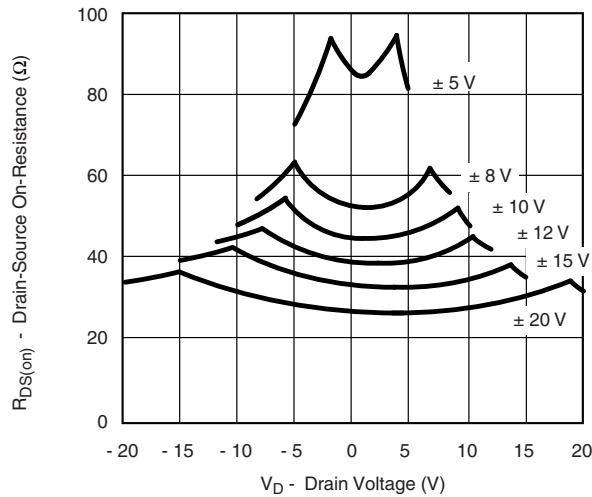
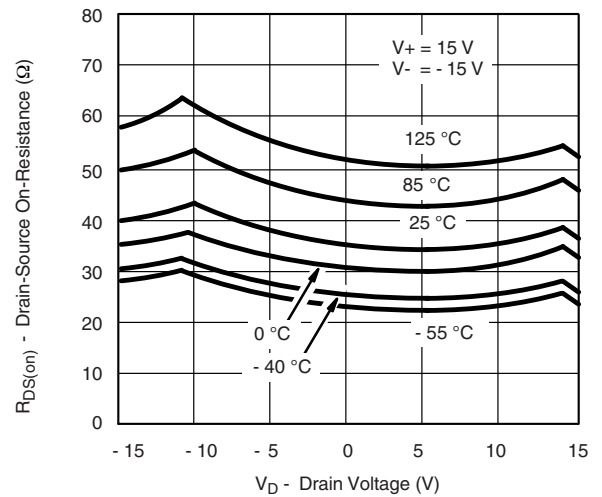
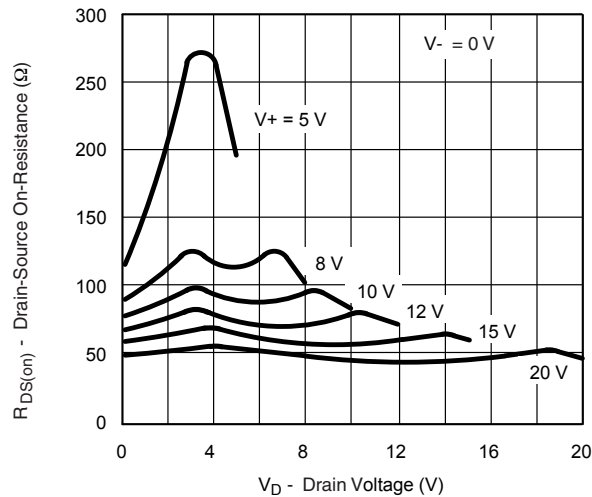
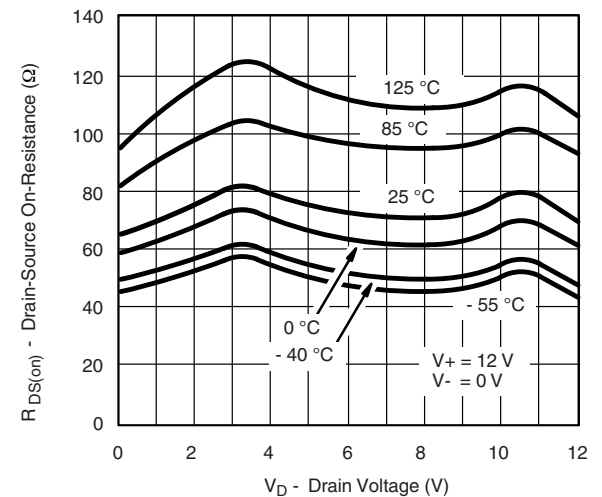
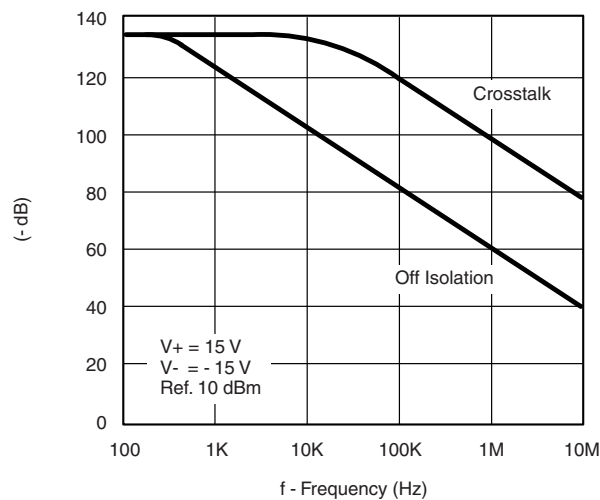
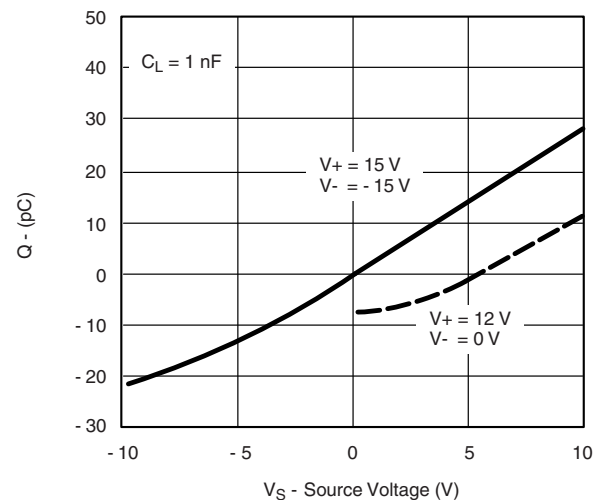
			Test Conditions Unless Otherwise Specified V ₊ = 15 V, V ₋ = - 15 V V _{IN} = 2.4 V, 0.8 V ^f		Temp. ^b	Typ. ^c	A Suffix - 55 °C to 125 °C		D Suffix - 40 °C to 85 °C		
Parameter		Symbol					Min. ^d	Max. ^d	Min. ^d	Max. ^d	Unit
Analog Switch											
Analog Signal Range ^e		V _{ANALOG}		Full			- 15	15	- 15	15	V
Drain-Source On-Resistance		R _{DS(on)}	I _S = - 10 mA, V _D = ± 8.5 V V ₊ = 13.5 V, V ₋ = - 13.5 V	Room Full	50			85 100		85 100	Ω
On-Resistance Match Between Channels ^e		ΔR _{DS(on)}	I _S = - 10 mA, V _D = ± 10 V V ₊ = 15 V, V ₋ = - 15 V	Room Full				4 5		4 5	
Switch Off Leakage Current		I _{S(off)}	V ₊ = 16.5, V ₋ = - 16.5 V V _D = ± 15.5 V, V _S = ± 15.5 V	Room Full	± 0.01	- 0.5 - 20	0.5 20	- 0.5 - 5	0.5 5	nA	
		I _{D(off)}		Room Full	± 0.01	- 0.5 - 20	0.5 20	- 0.5 - 5	0.5 5		
Channel On Leakage Current		I _{D(on)}	V ₊ = 16.5 V, V ₋ = - 16.5 V V _S = V _D = ± 15.5 V	Room Full	± 0.08	- 0.5 - 40	0.5 40	- 0.5 - 10	0.5 10		
Digital Control											
Input Current V _{IN} Low		I _{IL}	V _{IN} under test = 0.8 V, All Other = 2.4 V	Full	- 0.01	- 500	500	- 500	500	nA	
Input Current V _{IN} High		I _{IH}	V _{IN} under test = 2.4 V All Other = 0.8 V	Full	0.01	- 500	500	- 500	500		
Dynamic Characteristics											
Turn-On Time		t _{ON}	R _L = 1 kΩ, C _L = 35 pF V _S = ± 10 V See Figure 2	Room	150		250		250	ns	
Turn-Off Time	DG441	t _{OFF}		Room	90		120		120		
	DG442			Room	110		210		210		
Charge Injection ^e		Q	C _L = 1 nF, V _S = 0 V V _{gen} = 0 V, R _{gen} = 0 Ω	Room	- 1					pC	
Off Isolation ^e		OIRR	R _L = 50 Ω, C _L = 5 pF f = 1 MHz	Room	60					dB	
Crosstalk (Channel-to-Channel)		X _{TALK}		Room	100						
Source Off Capacitance ^e		C _{S(off)}	f = 1 MHz	Room	4					pF	
Drain Off Capacitance ^e		C _{D(off)}		Room	4						
Channel On Capacitance ^e		C _{D(on)}	V _{ANALOG} = 0 V	Room	16						
Power Supplies											
Positive Supply Current		I ₊	V ₊ = 16.5 V, V ₋ = - 16.5 V V _{IN} = 0 or 5 V	Full	15		100		100	μA	
Negative Supply Current		I ₋		Room Full	- 0.0001	- 1 - 5		- 1 - 5			
Ground Current		I _{GND}		Full	- 15	- 100		- 100			

SPECIFICATIONS ^a (Single Supply)									
Parameter	Symbol	Test Conditions Unless Otherwise Specified V ₊ = 12 V, V ₋ = 0 V V _{IN} = 2.4 V, 0.8 V ^f	Temp. ^b	Typ. ^c	A Suffix - 55 °C to 125 °C		D Suffix - 40 °C to 85 °C		Unit
					Min. ^d	Max. ^d	Min. ^d	Max. ^d	
Analog Switch									
Analog Signal Range ^e	V _{ANALOG}		Full		0	12	0	12	V
Drain-Source On-Resistance	R _{DS(on)}	I _S = - 10 mA, V _D = 3 V, 8 V V ₊ = 10.8 V	Room Full	100		160 200		160 200	Ω
Dynamic Characteristics									
Turn-On Time	t _{ON}	R _L = 1 kΩ, C _L = 35 pF V _S = 8 V See Figure 2	Room	300		450		450	ns
Turn-Off Time	t _{OFF}		Room	60		200		200	
Charge Injection	Q	C _L = 1nF, V _{gen} = 6 V, R _{gen} = 0 Ω	Room	2					pC
Power Supplies									
Positive Supply Current	I ₊	V ₊ = 13.2 V, V ₋ = 0 V V _{IN} = 0 or 5 V	Full	15		100		100	μA
Negative Supply Current	I ₋		Room Full	- 0.0001	- 1 - 100		- 1 - 100		
Ground Current	I _{GND}		Full	- 15	- 100		- 100		

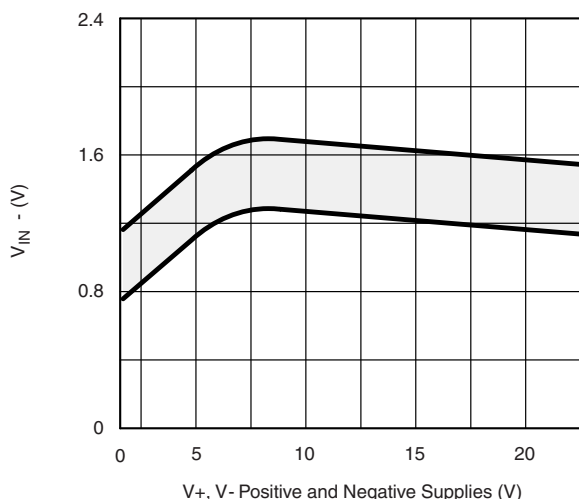
Notes:

- Refer to PROCESS OPTION FLOWCHART.
- Room = 25 °C, Full = as determined by the operating temperature suffix.
- Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- Guaranteed by design, not subject to production test.
- V_{IN} = input voltage to perform proper function.

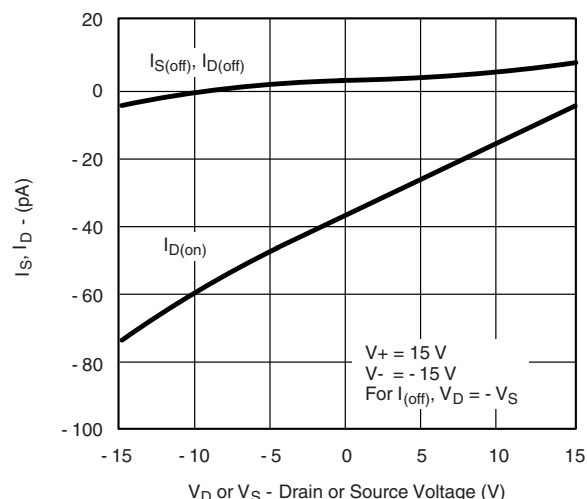
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

 $R_{DS(on)}$ vs. V_D and Power Supply Voltage

 $R_{DS(on)}$ vs. V_D and Temperature

 $R_{DS(on)}$ vs. V_D and Unipolar Power Supply Voltage

 $R_{DS(on)}$ vs. V_D and Temperature (Single 12-V Supply)

Crosstalk and Off Isolation vs. Frequency

Charge Injection vs. Source Voltage

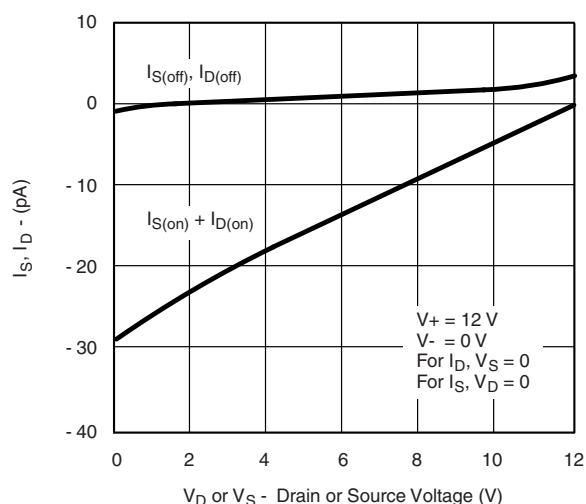
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



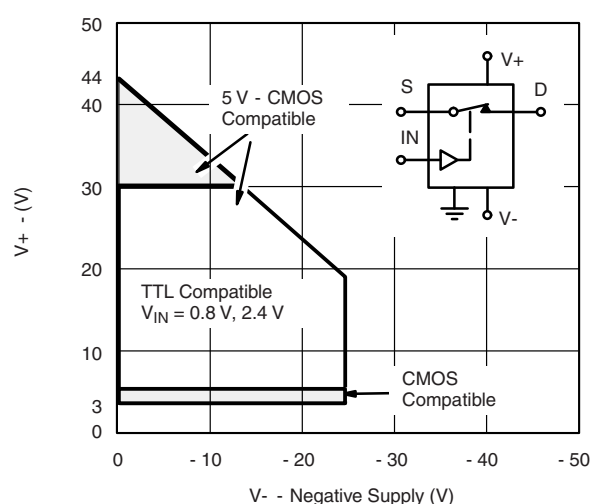
Switching Threshold vs. Supply Voltage



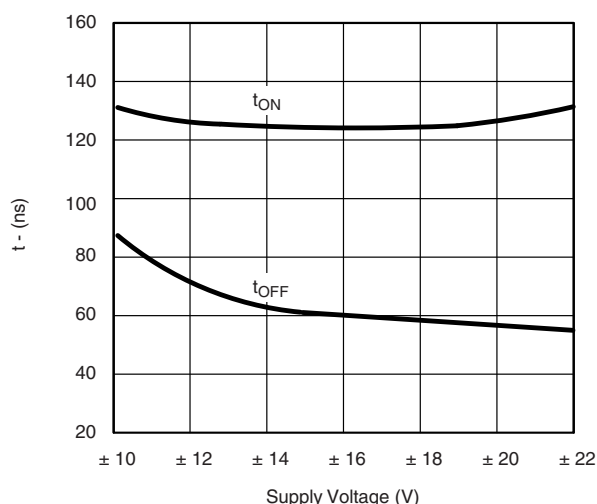
Source/Drain Leakage Currents



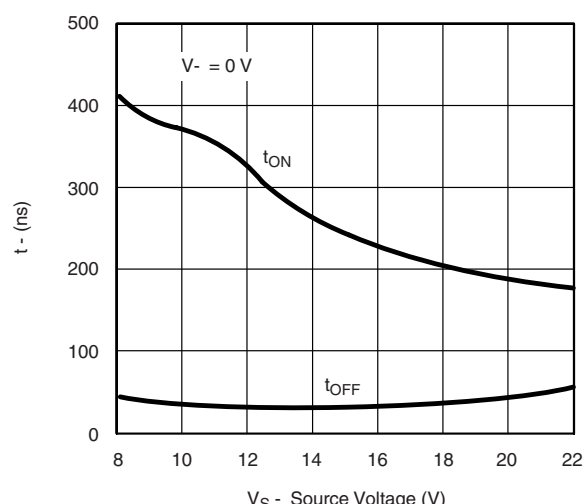
Source/Drain Leakage Currents (Single 12 V Supply)



Operating Voltage

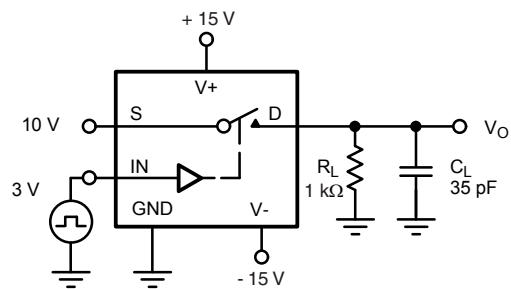


Switching Time vs. Power Supply Voltage

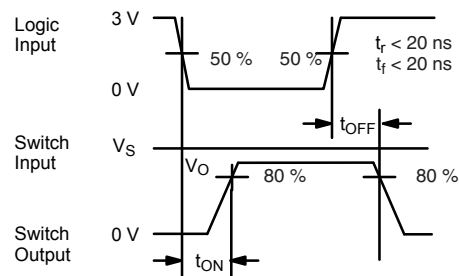


Switching Time vs. Power Supply Voltage

TEST CIRCUITS

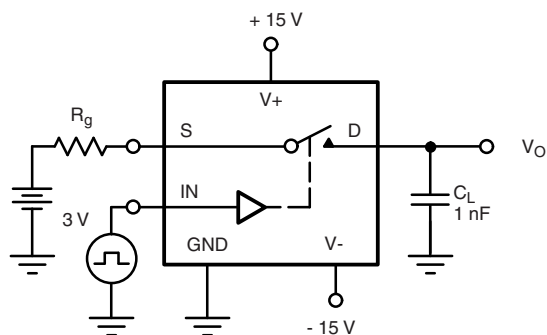


C_L (includes fixture and stray capacitance)



Note: Logic input waveform is inverted for DG442.

Figure 2. Switching Time



$C = 1$ mF tantalum in parallel with 0.01 mF ceramic

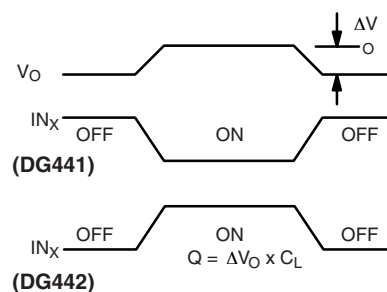
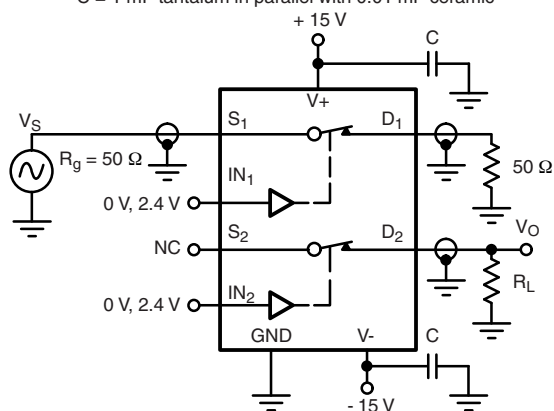
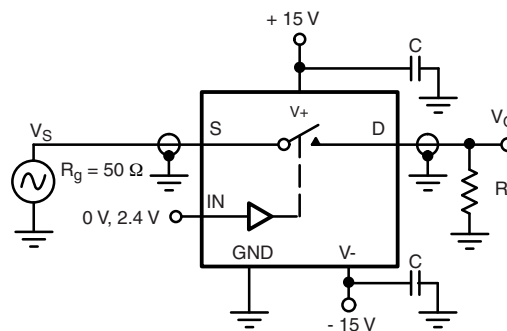


Figure 3. Charge Injection



$X_{TALK} \text{ Isolation} = 20 \log \left| \frac{V_S}{V_O} \right|$
C = RF bypass

Figure 4. Crosstalk



Off Isolation = $20 \log \left| \frac{V_S}{V_O} \right|$

Figure 5. Off Isolation

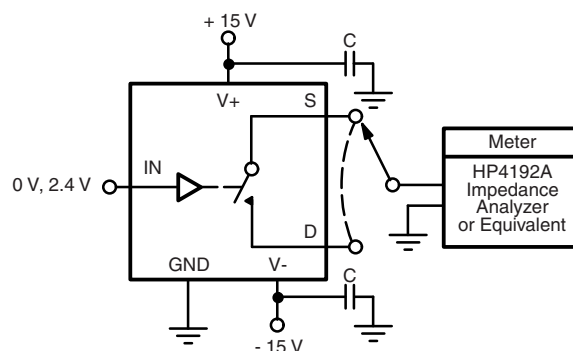


Figure 6. Source/Drain Capacitances

APPLICATIONS

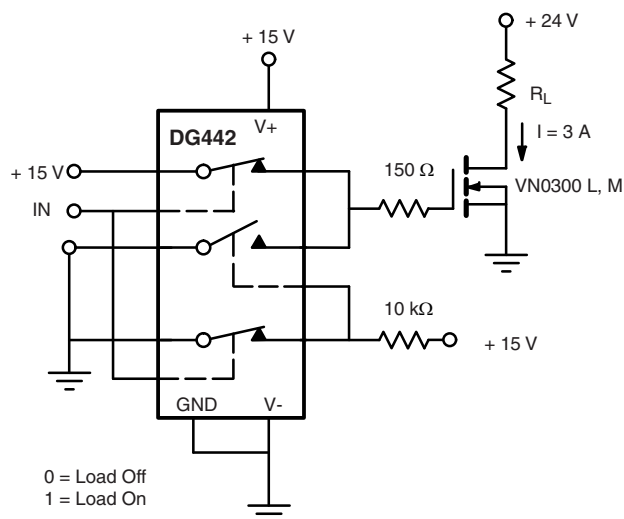


Figure 7. Power MOSFET Driver

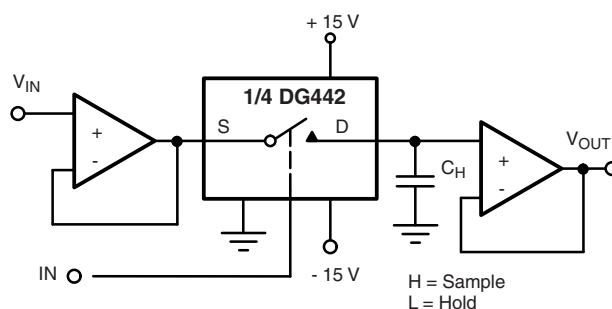


Figure 8. Open Loop Sample-and-Hold

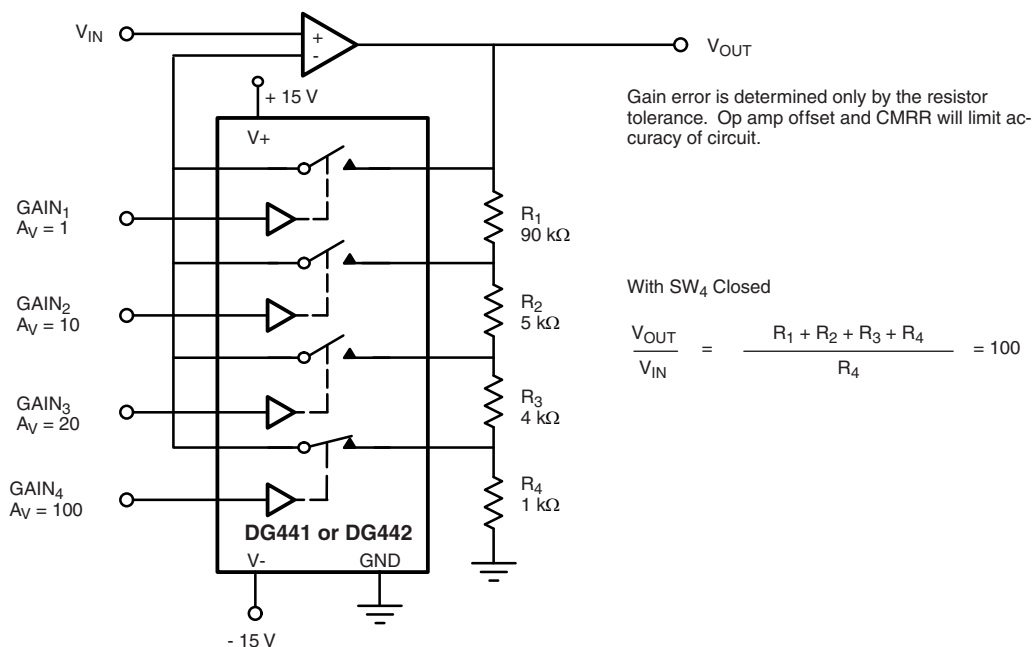


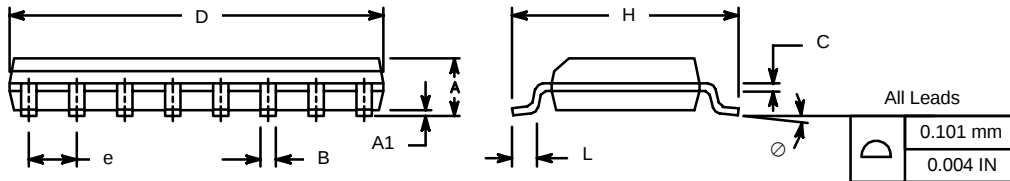
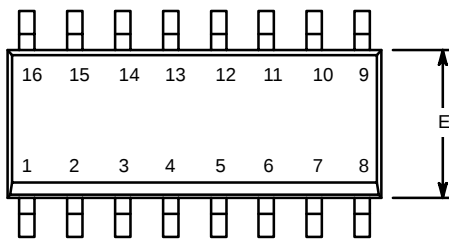
Figure 9. Precision-Weighted Resistor Programmable-Gain Amplifier

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?70053.



SOIC (NARROW): 16-LEAD

JEDEC Part Number: MS-012



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.38	0.51	0.015	0.020
C	0.18	0.23	0.007	0.009
D	9.80	10.00	0.385	0.393
E	3.80	4.00	0.149	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
L	0.50	0.93	0.020	0.037
Ø	0°	8°	0°	8°

ECN: S-03946—Rev. F, 09-Jul-01
DWG: 5300



PDIP: 16-LEAD

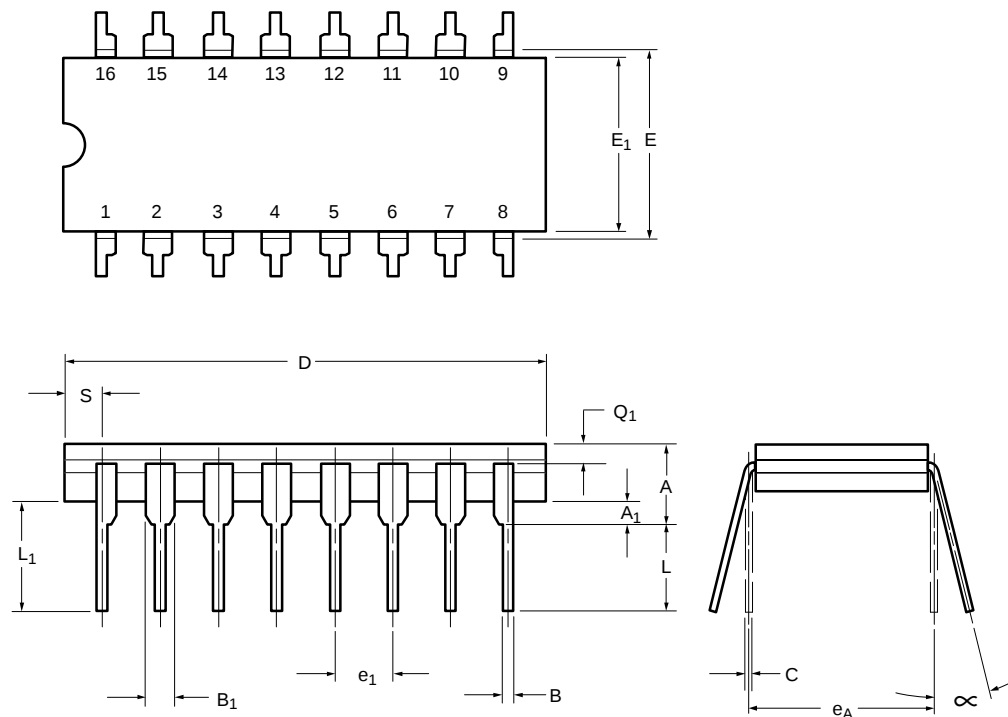


Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	3.81	5.08	0.150	0.200
A ₁	0.38	1.27	0.015	0.050
B	0.38	0.51	0.015	0.020
B ₁	0.89	1.65	0.035	0.065
C	0.20	0.30	0.008	0.012
D	18.93	21.33	0.745	0.840
E	7.62	8.26	0.300	0.325
E ₁	5.59	7.11	0.220	0.280
e ₁	2.29	2.79	0.090	0.110
e _A	7.37	7.87	0.290	0.310
L	2.79	3.81	0.110	0.150
Q ₁	1.27	2.03	0.050	0.080
S	0.38	1.52	.015	0.060

ECN: S-03946—Rev. D, 09-Jul-01
DWG: 5482



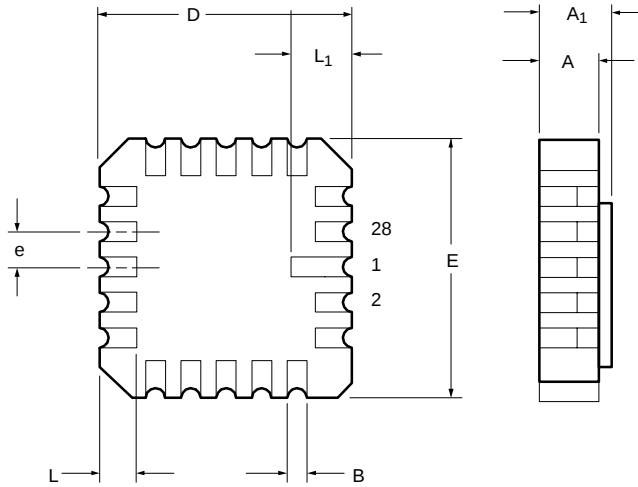
CERDIP: 16-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	4.06	5.08	0.160	0.200
A ₁	0.51	1.14	0.020	0.045
B	0.38	0.51	0.015	0.020
B ₁	1.14	1.65	0.045	0.065
C	0.20	0.30	0.008	0.012
D	19.05	19.56	0.750	0.770
E	7.62	8.26	0.300	0.325
E ₁	6.60	7.62	0.260	0.300
e ₁	2.54 BSC		0.100 BSC	
e _A	7.62 BSC		0.300 BSC	
L	3.18	3.81	0.125	0.150
L ₁	3.81	5.08	0.150	0.200
Q ₁	1.27	2.16	0.050	0.085
S	0.38	1.14	0.015	0.045
∞	0°	15°	0°	15°
ECN: S-03946—Rev. G, 09-Jul-01 DWG: 5403				



20-LEAD LCC



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.37	2.24	0.054	0.088
A₁	1.63	2.54	0.064	0.100
B	0.56	0.71	0.022	0.028
D	8.69	9.09	0.342	0.358
E	8.69	9.09	0.442	0.358
e	1.27 BSC		0.050 BSC	
L	1.14	1.40	0.045	0.055
L₁	1.96	2.36	0.077	0.093
ECN: S-03946—Rev. B, 09-Jul-01 DWG: 5321				

RECOMMENDED MINIMUM PADS FOR SO-16



Recommended Minimum Pads
Dimensions in Inches/(mm)

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Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.